

2SC5225

Silicon NPN Epitaxial Transistor

Application

- Wide band video output amplifier for color CRT monitor.
- High frequency high voltage amplifier.
- High speed power switching.
- Complementary pair with 2SA1960.

Features

- High voltage large current operation.
 $V_{CEO} = 80 \text{ V}$, $I_C = 300 \text{ mA}$
- High f_T .
 $f_T = 1.4 \text{ GHz}$
- Small output capacitance.
 $C_{ob} = 3 \text{ pF}$

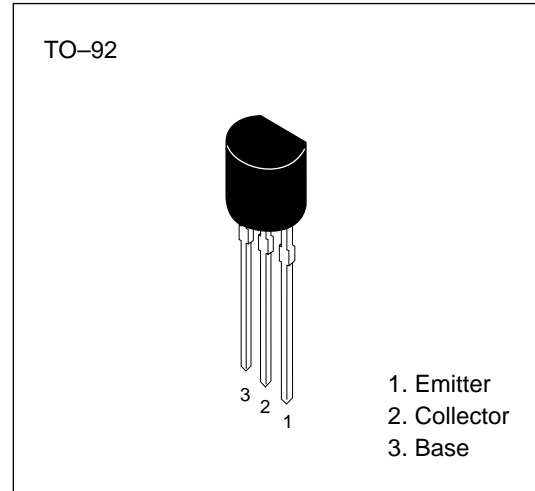


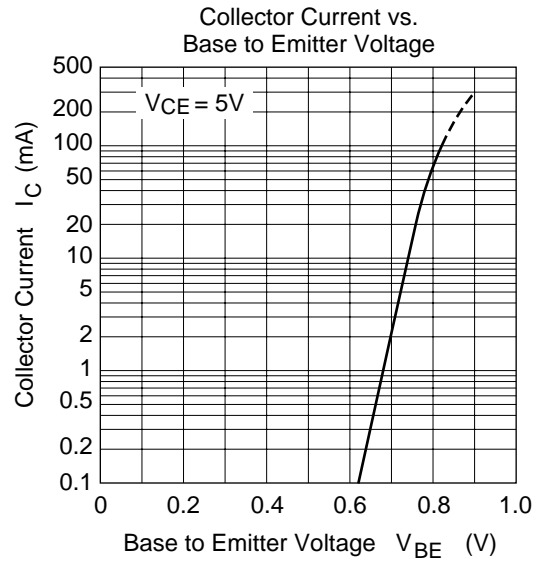
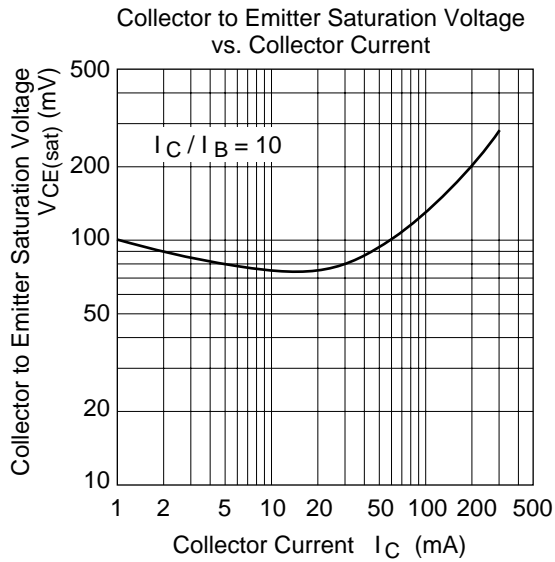
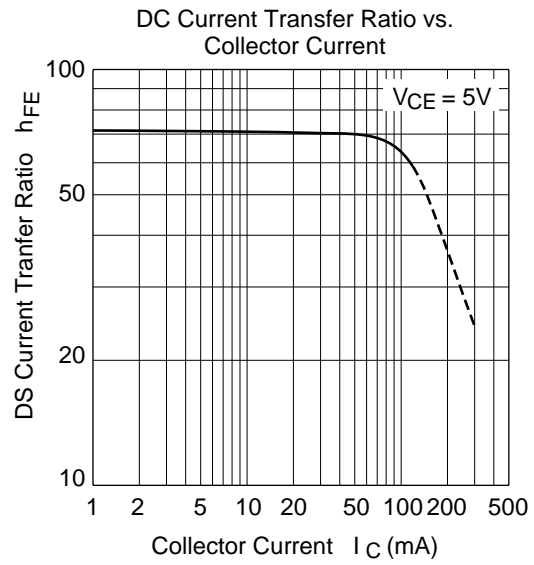
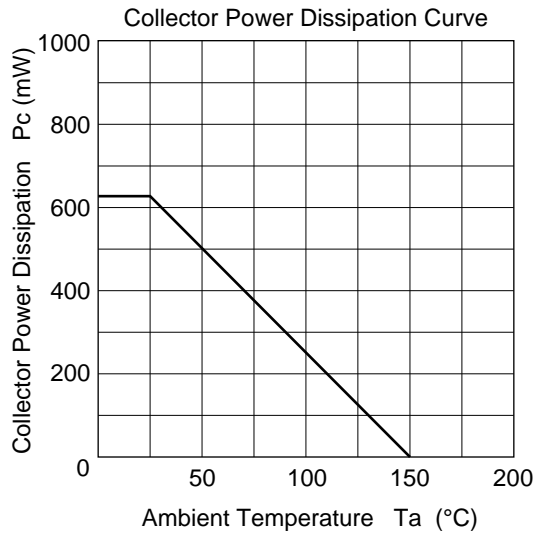
Table 1 Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	100	V
Collector to emitter voltage	V_{CEO}	80	V
Emitter to base voltage	V_{EBO}	3	V
Collector current	I_C	300	mA
Collector power dissipation	P_C	625	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

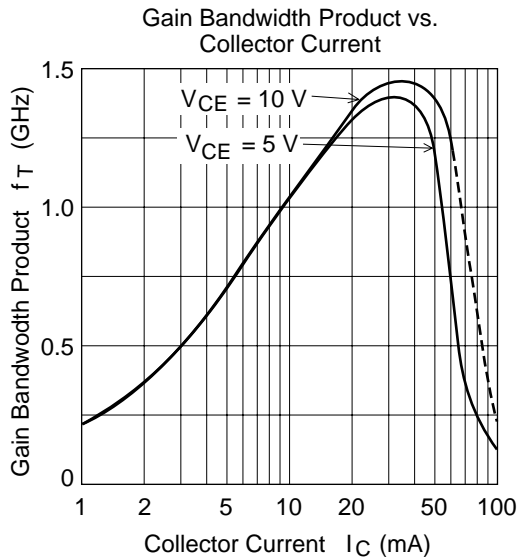
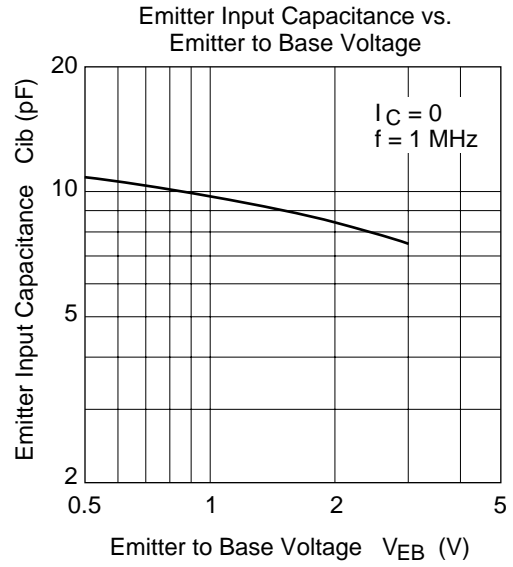
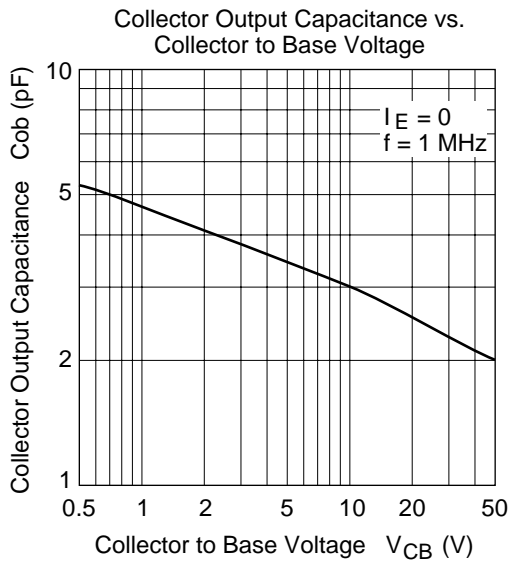
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Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	100	—	—	V	$I_C = 100 \mu A$ $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	80	—	—	V	$I_C = 1 \text{ mA}$ $R_{BE} = \infty$
Collector to base cutoff current	I_{CBO}	—	—	1.0	μA	$V_{CB} = 80 \text{ V}$ $I_E = 0$
Emitter to base cutoff current	I_{EBO}	—	—	10	μA	$V_{EB} = 3 \text{ V}$ $I_C = 0$
DC current transfer ratio	h_{FE}	20	70	—		$V_{CE} = 5 \text{ V}$, $I_C = 50 \text{ mA}$ Pulse test
Gain bandwidth product	f_T	1.2	1.4	—	GHz	$V_{CE} = 10 \text{ V}$ $I_C = 50 \text{ mA}$
Emitter input capacitance	C_{ib}	—	13	19	pF	$V_{EB} = 0$ $f = 1 \text{ MHz}$ $I_C = 0$
Collector output capacitance	C_{ob}	—	3	4.0	pF	$V_{CB} = 10 \text{ V}$ $f = 1 \text{ MHz}$ $I_E = 0$



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Package Dimensions

Unit : mm

